

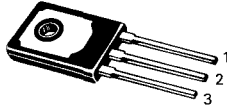
ALPHANUMERIC INDEX — CROSS-REFERENCE (Continued)

Industry Part Number	Motorola Direct Replacement	Motorola Similar Replacement	Page Number	Industry Part Number	Motorola Direct Replacement	Motorola Similar Replacement	Page Number
MJF127	MJF127		3-1016	MPS-U60	MPS-U60		3-1066
MJF15030	MJF15030		3-1026	MPS-U95	MPS-U95		3-1068
MJF15031	MJF15031		3-1026	MPSU01	MPS-U01		3-1040
MJF2955	MJF2955		—	MPSU01A	MPS-U01A		3-1040
MJF3055	MJF3055		—	MPSU02	MPS-U02		3-1042
MJF47	MJF47		3-1007	MPSU03	MPS-U03		3-1044
MJF6107	MJF6107		3-1022	MPSU04	MPS-U04		3-1044
MJH10012	MJH10012		3-596	MPSU05	MPS-U05		3-1048
MJH11017	MJH11017		3-1034	MPSU06	MPS-U06		3-1048
MJH11018	MJH11018		3-1034	MPSU07	MPS-U07		3-1050
MJH11019	MJH11019		3-1034	MPSU10	MPS-U10		3-1052
MJH11020	MJH11020		3-1034	MPSU11		MPS-U10	3-1052
MJH11021	MJH11021		3-1034	MPSU12		MPS-U45	3-1055
MJH11022	MJH11022		3-1034	MPSU45	MPS-U45		3-1055
MJH12004	MJH12004		3-644	MPSU51	MPS-U51		3-1058
MJH12005	MJH12005		—	MPSU51A	MPS-U51A		3-1058
MJH13090	MJH13090		3-688	MPSU52	MPS-U52		3-1060
MJH13091	MJH13091	MJH16010	3-758	MPSU55	MPS-U55		3-1062
MJH16002	MJH16002		3-976	MPSU56	MPS-U56		3-1062
MJH16002A	MJH16002A		3-734	MPSU57	MPS-U57		3-1064
MJH16004	MJH16004		3-976	MPSU60	MPS-U60		3-1066
MJH16006	MJH16006		3-742	MPSU95	MPS-U95		3-1068
MJH16006A	MJH16006A		3-750	NSD102		2N4923	3-79
MJH16008	MJH16008		3-742	NSD103		2N4923	3-79
MJH16010	MJH16010		3-758	NSD104		2N4923	3-79
MJH16010A	MJH16010A		3-766	NSD105		2N4923	3-79
MJH16012	MJH16012		3-758	NSD106		2N4923	3-79
MJH16018	MJH16018		3-782	NSD131		MJE340	3-876
MJH16032	MJH16032		3-984	NSD132		MJE340	3-876
MJH16034	MJH16034		3-984	NSD133		MJE340	3-876
MJH6282	MJH6282		3-1030	NSD134		MJE340	3-876
MJH6283	MJH6283		3-1030	NSD135		MJE340	3-876
MJH6284	MJH6284		3-1030	NSD151		MJE800	3-888
MJH6285	MJH6285		3-1030	NSD152		MJE800	3-888
MJH6286	MJH6286		3-1030	NSD202		2N4919	3-75
MJH6287	MJH6287		3-1030	NSD203		2N4919	3-75
MJH6676	MJH16010		3-758	NSD204		2N4919	3-75
MJH6677	MJH16010		3-758	NSD205		2N4919	3-75
MJH6678	MJH16010		3-758	NSD206		2N4919	3-75
MPC900		2N6050	3-143	NSD3439		MJE3439	3-908
MPS-U01	MPS-U01		3-1040	NSD3440		MJE3440	3-908
MPS-U01A	MPS-U01A		3-1040	NSDU01		MPS-UC1	3-1040
MPS-U02	MPS-U02		3-1042	NSDU01A		MPS-UC1A	3-1040
MPS-U03	MPS-U03		3-1044	NSDU05		MPS-U05	3-1048
MPS-U04	MPS-U04		3-1044	NSDU06		MPS-U06	3-1048
MPS-U05	MPS-U05		3-1048	NSDU07		MPS-U07	3-1050
MPS-U06	MPS-U06		3-1048	NSDU45		MPS-U45	3-1055
MPS-U07	MPS-U07		3-1050	NSDU51		MPS-U51	3-1058
MPS-U10	MPS-U10		3-1052	NSDU51A		MPS-U51A	3-1058
MPS-U11		MPS-U10	3-1052	NSDU55		MPS-U55	3-1062
MPS-U12		MPS-U45	3-1055	NSDU56		MPS-U56	3-1062
MPS-U31		MPS-U06	3-1048	NSDU57		MPS-U57	3-1064
MPS-U45	MPS-U45		3-1055	NSE170		MJE170	3-862
MPS-U47		MPS-U06	3-1048	NSE171		MJE171	3-862
MPS-U51	MPS-U51		3-1058	NSE180		MJE180	3-862
MPS-U51A	MPS-U51A		3-1058	NSE181		MJE181	3-862
MPS-U52	MPS-U52		3-1060	NSP105		TIP42A	3-1083
MPS-U55	MPS-U55		3-1062	NSP2010		TIP42	3-1083
MPS-U56	MPS-U56		3-1062	NSP2011		TIP42A	3-1083
MPS-U57	MPS-U57		3-1064	NSP2021		TIP41A	3-1083

*Consult Motorola if a direct replacement is necessary.

TABLE 8 — PLASTIC TO-225 Type (Formerly TO-127 Type)†

STYLE 2:
PIN 1. EMITTER
2. COLLECTOR
3. BASE



CASE 90-05 (TO-225AB)

I _C Cont Amps Max	V _{CEO(sus)} Volts Min	Device Type		h _{FE} Min/Max	@ I _C Amp	Resistive Switching			f _T MHz Min	P _D (Case) Watts @ 25°C
		NPN	PNP			t _s μs Max	t _f μs Max	@ I _C Amp		
		5	50				MJE105	25/100		
	60	MJE1100##	MJE1090##	750 min	3A				1	70
		MJE1101##		750 min	4A				1	70
	80	MJE1102##	MJE1092##	750 min	3A				1	70
		MJE1103##	MJE1093##	750 min	4A				1	70
8	60	MJE6043##	MJE6040##	1k/20k	4	1.5 typ	1.5 typ	4	4#	75
	80	MJE6044##	MJE6041##	1k/20k	4	1.5 typ	1.5 typ	4	4#	75
	100	MJE6045##		1k/20k	4	1.5 typ	1.5 typ	4	4#	75
10	60	MJE2801	MJE2901	25/100	3					90
		MJE3055	MJE2955	20/70	4				2	90
12	40	2N5989		20/120	6	0.5 typ	0.25 typ	6	2	100
	80	2N5991		20/120	6	0.5 typ	0.25 typ	6	2	100
15	40	MJE1660		20/100	5				3	90
	60	MJE1661		20/100	5				3	90

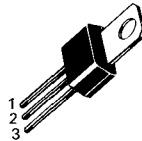
|h_{FE}| @ 1 MHz, ## Darlington

† Not recommended for new designs (check TO-220, Table 5 for alternates)

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TABLE 9 — PLASTIC CASE 152†

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR



(COLLECTOR CONNECTED TO TAB)

I _C Cont Amps Max	V _{CEO(sus)} Volts Min	Device Type		h _{FE} Min/Max	@ I _C Amp	Resistive Switching			f _T MHz Min	P _D (Case) Watts @ 25°C
		NPN	PNP			t _s μs Max	t _f μs Max	@ I _C Amp		
		0.5	300			MPS-U10	MPS-U60	30 min		
0.8	40	MPS-U02	MPS-U52	30 min	0.5				150	10
1	120	MPS-U03		40 min	0.01				100	10
	180	MPS-U04		40 min	0.01				100	10
2	30	MPS-U01	MPS-U51	50 min	1				50	10
	40	MPS-U01A	MPS-U51A	50 min	1				50	10
		MPS-U45##	MPS-U95##	4k min	1				100	10

Darlington

(continued)

† Not recommended for new designs (check TO-225, Table 7 or TO-220, Table 5 for alternates)

TABLE 11 — MILITARY SPECIFIED POWER TRANSISTORS (continued)

I _C Cont Amps Max	V _{CEO} (sus) Volts Min	Device Type		hFE Min/Max	@ I _C Amp	Resistive Switching			f _T MHz Min	P _D (Case) Watts @ 25°C	Case JEDEC/MOT
		NPN/#	PNP/#			t _s μs Max	t _f μs Max	@ I _C Amp			
15	400	2N6547J,/525 TX		12/60	5	4.7*		10	6	175	TO-204/1
		2N6675J,/537 TX, TXV**		8/20	10	2.5	0.5	10	15	175	TO-204AA/1
20	75	2N5039J,/439 TX, TXV		30/150	2	2*		10	60	140	TO-204/1
	80	2N5303J,/456A TX, TXV	2N5745J,/433 TX, TXV	15/60	10	3*		10	2	200	TO-204/1
		2N6283J,/504 TX, TXV	2N6286J,/505 TX, TXV	1250/18k	10	10*		10	8	175	TO-204/1
	90	2N5038J,/439 TX, TXV		50/200	2	2*		12	60	140	TO-204/1
25	100		2N6437J,/508 TX, TXV	30/120	10	1		10	40	200	TO-204/1
	120		2N6438J,/509 TX, TXV	30/120	10	1		10	40	200	TO-204/1
30	60	2N5302J,/456A TX, TXV	2N4399J,/433 TX, TXV	15/60	15	3*		10	2	200	TO-204/1
50	60	2N5685J,/464 TX, TXV	2N5683J,/466 TX, TXV	15/60	25	3*		25	2	300	TO-204/197
	80	2N5686J,/464 TX, TXV	2N5684J,/466 TX, TXV	15/60	25	3*		25	2	300	TO-204/197
	100	2N6274J,/514 TX, TXV	2N6378J,/515 TX, TXV	30/120	20	1.05*		20	30	250	TO-204/197
	120		2N6379J,/515 TX, TXV	30/120	20	1.05*		20	30	250	TO-204/197
	150	2N6277J,/514 TX, TXV**		30/120	20	1.05*		20	30	250	TO-204/197

MIL-S-19500 Detailed
Spec. shown by
Device Type

* t_{off}

** Consult
Factory for
qualification
status.

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TABLE 12 — POWER DARLINGTONS

I _C Cont Amps Max	V _{CEO} (sus) Volts Min	Device Type		hFE Min/Max	@ I _C Amp	Resistive Switching			h _{fe} @ 1 MHz Min	P _D (Case) Watts @ 25°C	Case JEDEC/MOT
		NPN	PNP			t _s μs Max	t _f μs Max	@ I _C Amp			
2	40	MPS-U45	MPS-U95	4k min	1				100	10	/152
	60	TIP110	TIP115	1k min	1	2 typ	1 typ	1	25	50	TO-220/221A
	80	TIP111	TIP116	1k min	1	2 typ	1 typ	1	25	50	TO-220/221A
	100	TIP112 MJD112 MJE270	TIP117 MJD117 MJE271	1k min 1000 min 1.5k min	1 2 0.12	2 typ 1.7 typ	1 typ 1.3 typ	1 2	25 25 6	50 20 25	TO-220/221A TO-252/369A-04 TO-225AA/77

(continued)

TABLE 12 — POWER DARLINGTONS (continued)

I _C Cont Amps Max	V _{CEO(sus)} Volts Min	Device Type		h _{FE} Min/Max	@ I _C Amp	Resistive Switching			h _{FE} @ 1 MHz Min	P _D (Case) Watts @ 25°C	Case JEDEC/MOT
		NPN	PNP			t _s μs Max	t _f μs Max	@ I _C Amp			
		50	90			MJ11030	MJ11031	400 min			
	120	MJ11032	MJ11033	400 min	50					300	TO-204/197
	400	MJ10015*		10 min	40	2.5	0.5	20	10	250	TO-204/197
	500	BUT34*		15 min	32	3	1.5	32		250	TO-204/197
		MJ10016*		10 min	40	2.5	0.5	20	10	250	TO-204/197
56	400	BUT33*		20 min	36	3.3	1.6	36		250	TO-204/197
60	200	MJ10020*		75/1k min	15	3.5	0.5	30		250	TO-204/197
	250	MJ10021*		75/1k min	15	3.5	0.5	30		250	TO-204/197

* Darlington with speed-up diode.

TABLE 13 — POWER SWITCHING TRANSISTORS

V_{CEO} < 200 V

I _C Cont Amps Max	V _{CEO(sus)} Volts Min	Device Type		h _{FE} Min/Max	@ I _C Amp	Resistive Switching			t _r MHz Min	P _D (Case) Watts @ 25°C	Case JEDEC/MOT
		NPN	PNP			t _s μs Max	t _f μs Max	@ I _C Amp			
0.8	40	MPS-U02	MPS-U52	30 min	0.5				150	10	—/152
1	120	MPS-U03		40 min	0.1				100	10	—/152
	180	MPS-U04		40 min	0.1				100	10	—/152
2	30	MPS-U01	MPS-U51	50 min	1				50	10	—/152
	40	MPS-U01A	MPS-U51A	50 min	1				50	10	—/152
		MPS-U45#	MPS-U95#	4k min	1				100	10	—/152
	60	MPS-U05	MPS-U55	60 min	0.25				50	10	—/152
	80	MPS-U06	MPS-U56	60 min	0.25				50	10	—/152
3	40		2N3719	25/180	2	0.4*		1	60	6	TO-205AA/31
			2N3867	40/200	2	0.4*		1	60	6	TO-205AA/31
	60		2N3720	25/180	2	0.4*		1	60	6	TO-205AA/31
			2N3868	30/150	2	0.4*		1	60	6	TO-205AA/31
	80		2N6303	30/150	2	0.4*		1	60	6	TO-205AA/31

Darlington

* t_{off} @ 1 MHz

(continued)

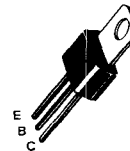
**NOT RECOMMENDED
 FOR NEW DESIGNS**

**PNP SILICON DARLINGTON
 AMPLIFIER TRANSISTOR**

... designed for amplifier and driver applications.

- High DC Current Gain –
 $h_{FE} = 25,000$ (Min) @ $I_C = 200$ mA dc
 $15,000$ (Min) @ $I_C = 500$ mA dc
- Collector-Emitter Breakdown Voltage –
 $V_{(BR)CES} = 40$ Vdc (Min) @ $I_C = 100$ μ A dc
- Low Collector-Emitter Saturation Voltage –
 $V_{CE(sat)} = 1.5$ Vdc @ $I_C = 1.0$ A dc
- Monolithic Construction for High Reliability
- Complement to NPN MPS-U45

**PNP SILICON
 DARLINGTON
 TRANSISTOR**



MAXIMUM RATINGS

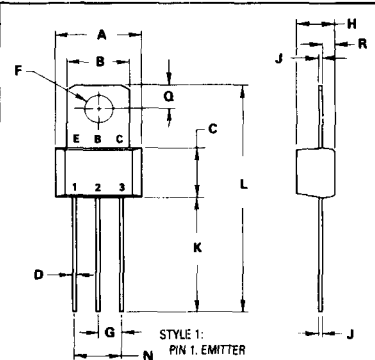
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}^{(1)}$	40	Vdc
Collector-Emitter Voltage	V_{CES}	40	Vdc
Collector-Base Voltage	V_{CB}	50	Vdc
Emitter-Base Voltage	V_{EB}	10	Vdc
Collector Current -Continuous	I_C	2.0	A dc
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.0 8.0	Watt mW/ $^\circ\text{C}$
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	10 80	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA(2)}$	125	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	12.5	$^\circ\text{C/W}$

- (1) Due to the monolithic construction of this device, breakdown voltages of both transistor elements are identical. $V_{(BR)CES}$ is tested in lieu of $V_{(BR)CEO}$ in order to avoid errors caused by noise pickup. The voltage measured during the $V_{(BR)CES}$ test is the $V_{(BR)CEO}$ of the output transistor.
- (2) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

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NOTE:

1. LEADS WITHIN 0.15 mm(0.006) TOTAL OF TRUE POSITION AT CASE, AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	9.14	9.53	0.360	0.375
B	6.60	7.24	0.260	0.285
C	5.41	5.66	0.213	0.223
D	0.38	0.53	0.015	0.021
F	3.18	3.33	0.125	0.131
G	2.54 BSC		0.100 BSC	
H	3.94	4.19	0.155	0.165
J	0.36	0.41	0.014	0.016
K	11.63	12.70	0.458	0.500
L	24.58	25.53	0.968	1.005
N	5.08 BSC		0.200 BSC	
O	2.39	2.69	0.094	0.106
R	1.14	1.40	0.045	0.055

CASE 152-02

MPS-U95

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage (I _C = 100 μAdc, V _{BE} = 0)	V _{(BR)CES}	40	—	—	Vdc
Collector-Base Breakdown Voltage (I _C = 100 μAdc, I _E = 0)	V _{(BR)CBO}	50	—	—	Vdc
Emitter-Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)	V _{(BR)EBO}	10	—	—	Vdc
Collector Cutoff Current (V _{CB} = 30 Vdc, I _E = 0)	I _{CBO}	—	—	100	nAdc
Emitter Cutoff Current (V _{EB} = 8.0 Vdc, I _C = 0)	I _{EBO}	—	—	100	nAdc

ON CHARACTERISTICS(1)

DC Current Gain (I _C = 200 mAdc, V _{CE} = 5.0 Vdc) (I _C = 500 mAdc, V _{CE} = 5.0 Vdc) (I _C = 1.0 Adc, V _{CE} = 5.0 Vdc)	h _{FE}	25,000 15,000 4,000	43,000 41,000 35,000	150,000 — —	—
Collector-Emitter Saturation Voltage (I _C = 1.0 Adc, I _B = 2.0 mAdc)	V _{CE(sat)}	—	1.0	1.5	Vdc
Base-Emitter Saturation Voltage (I _C = 1.0 Adc, I _B = 2.0 mAdc)	V _{BE(sat)}	—	1.85	2.0	Vdc
Base-Emitter On Voltage (I _C = 1.0 Adc, V _{CE} = 5.0 Vdc)	V _{BE(on)}	—	1.7	2.0	Vdc

DYNAMIC CHARACTERISTICS

Small-Signal Current Gain (1) (I _C = 200 mAdc, V _{CE} = 5.0 Vdc, f = 100 MHz)	h _{fe}	0.5	1.6	—	—
Collector Base Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)	C _{cb}	—	2.5	12	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

Uniwatt Darlington transistors can be used in any number of low power applications, such as relay drivers, motor control and as general purpose amplifiers. As an audio amplifier these devices, when used as a complementary pair, can drive 3.5 watts into a 3.2 ohm speaker using a 14 volt supply with less than one percent distortion. Because of the high gain the base drive requirement is as low as 1 mA in this application. They are also useful as power drivers for high current application such as voltage regulators.

FIGURE 1 – DC CURRENT GAIN

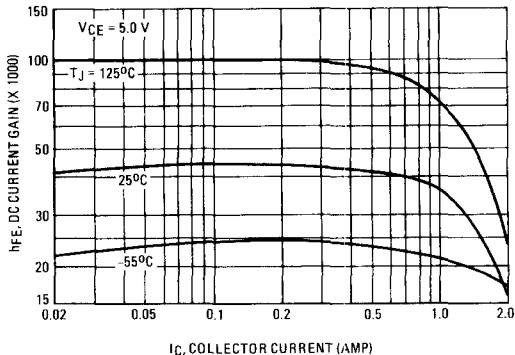


FIGURE 2 – SMALL-SIGNAL CURRENT GAIN

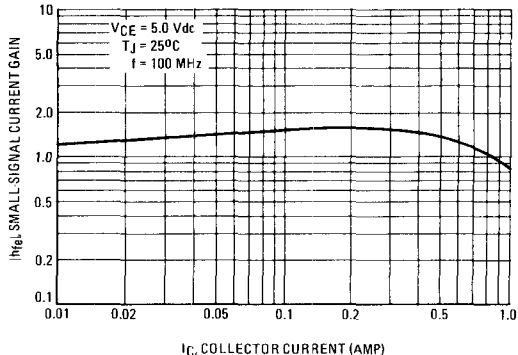


FIGURE 3 – "ON" VOLTAGES

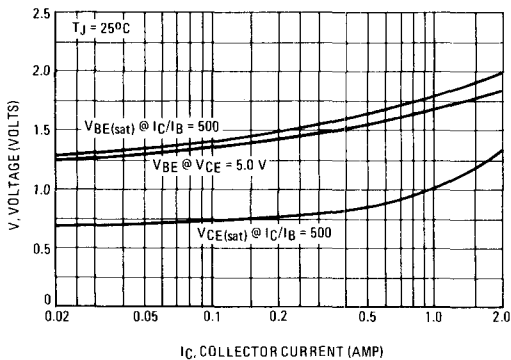


FIGURE 4 – TEMPERATURE COEFFICIENT

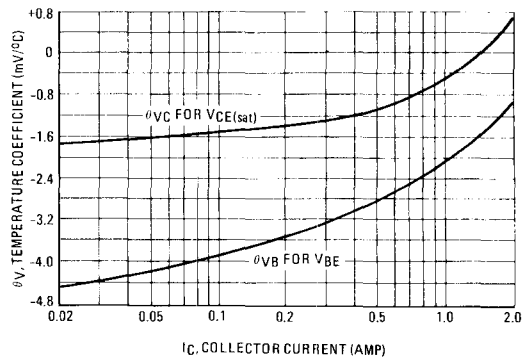
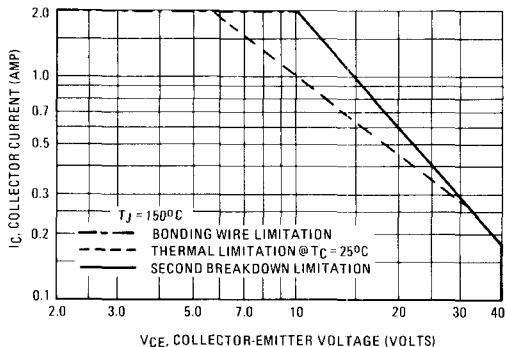


FIGURE 5 – DC SAFE OPERATING AREA



There are two limitations on the power handling ability of a transistor: junction temperature and second breakdown. Safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on T_{J(pk)} = 150°C; T_C is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.